

# Concepts in Mesoscopic Physics

## Drude Conductivity

$$\sigma = en\mu = \frac{ne^2\tau_m}{m^*}$$

rewrite using  $k_F = \sqrt{2\pi n}$

$$\ell = v_F\tau_m$$

$$v_F = \frac{\hbar k_F}{m^*}$$

$$\sigma = g_s g_v \frac{e^2}{h} \frac{k_F \ell}{2} = \frac{2e^2}{h} \frac{k_F \ell}{2}$$

rewrite using

$$\rho_{DOS} = \frac{g_s g_v m^*}{2\pi\hbar^2} = \frac{m^*}{\pi\hbar^2}$$

$$D = \frac{1}{2}v_F^2\tau_m = \frac{1}{2}v_F\ell$$

$$\sigma = e^2 \rho_{DOS}(E) D$$

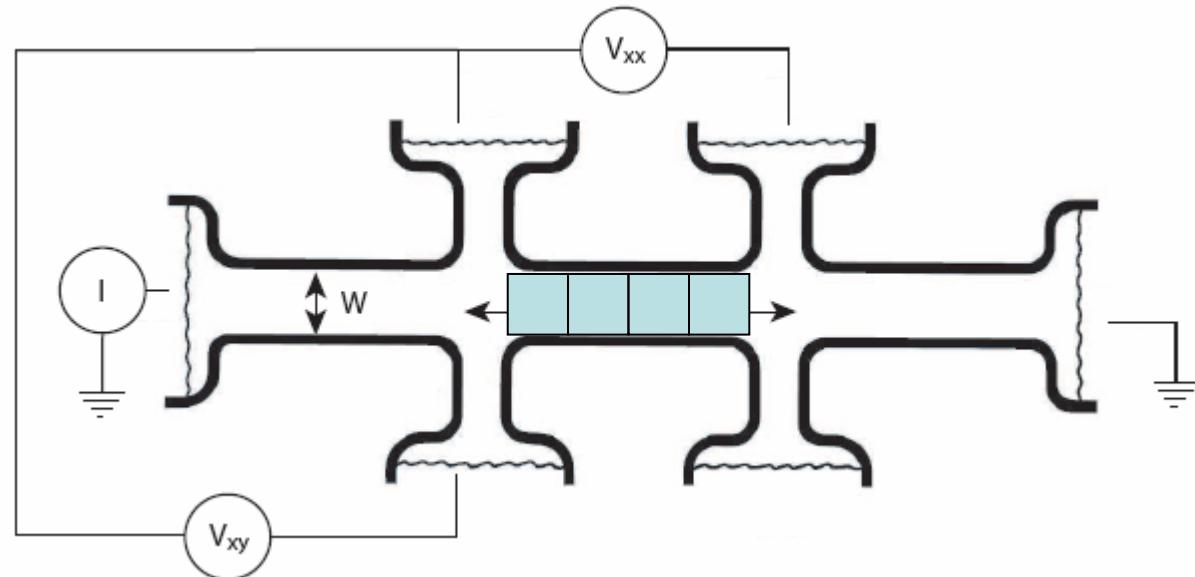
# Resistance per Square

2D: resistivity and resistance: same units

$$R = \rho \frac{L}{W} = \rho \square \frac{L}{W}$$

$\rho \square$  resistance per square

example: Hall bar



# Mesoscopic Time and Length Scales

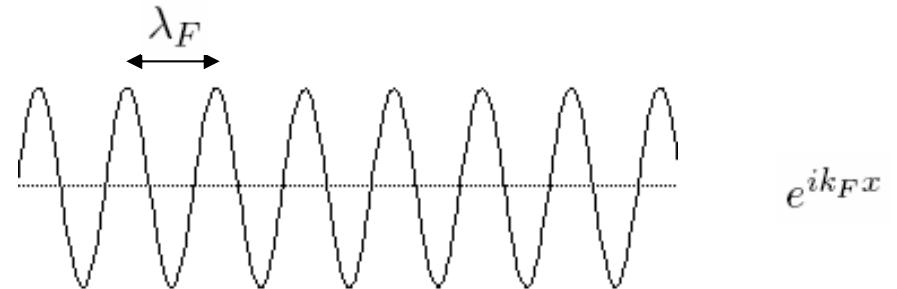
Fermi wavelength  $\lambda_F$

$$\lambda_F = 2\pi/k_F = \sqrt{2\pi/n}$$

Typically,  $n \sim 2 \times 10^{11} \text{ cm}^{-2} = 2 \times 10^{15} \text{ m}^{-2}$      $\lambda_F \sim 56 \text{ nm}$

$$E_F \sim 7 \text{ meV}$$

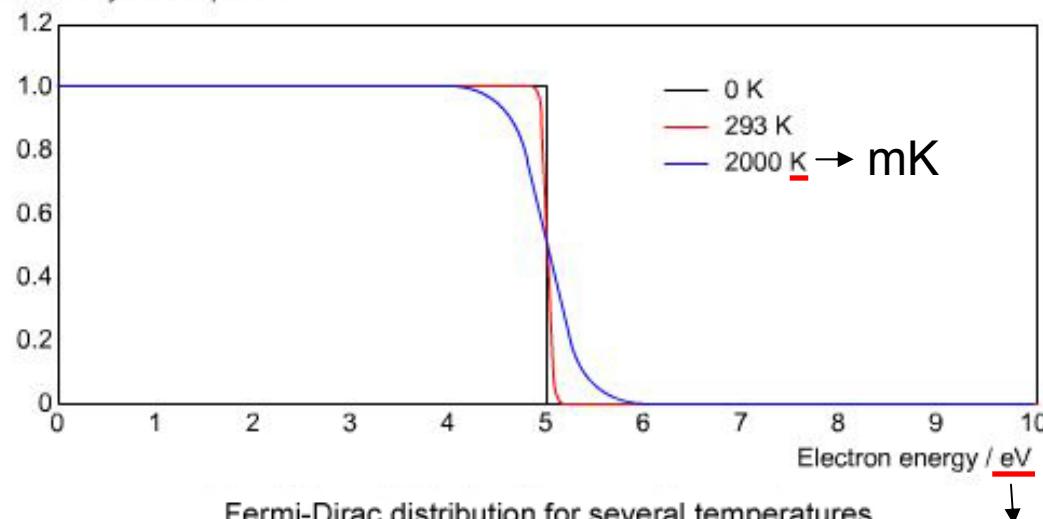
$$m^* = 0.067m_e$$



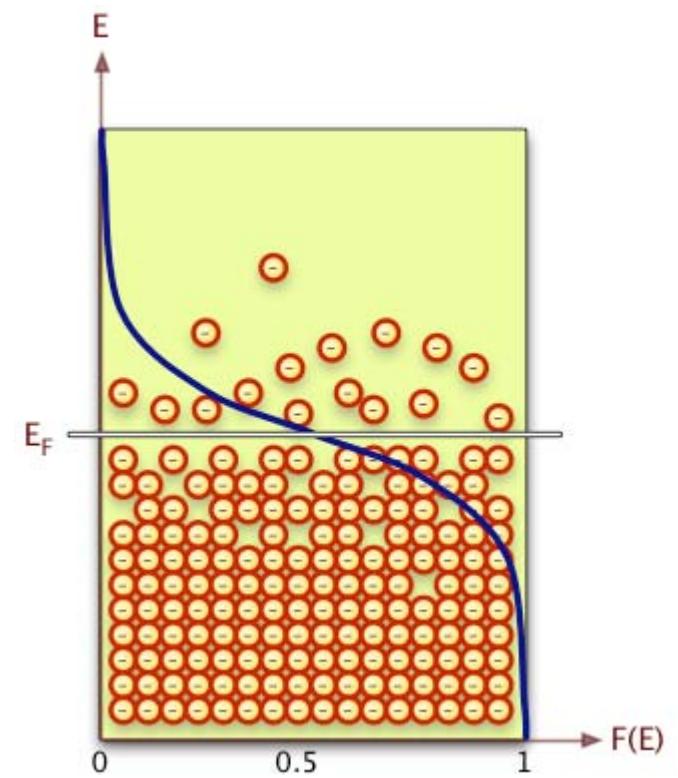
Fermi-Dirac distribution

$$\frac{1}{e^{(E-E_F)/kT} + 1}$$

Probability of occupation



Fermi-Dirac distribution for several temperatures



# Mesoscopic Time and Length Scales

Mean free path  $\ell$

$$\ell = v_F \tau_m = v_F \mu \frac{m^*}{e}$$

$$\mu = 100 \text{ m}^2/(\text{Vs}) = 1'000'000 \text{ cm}^2/(\text{Vs})$$

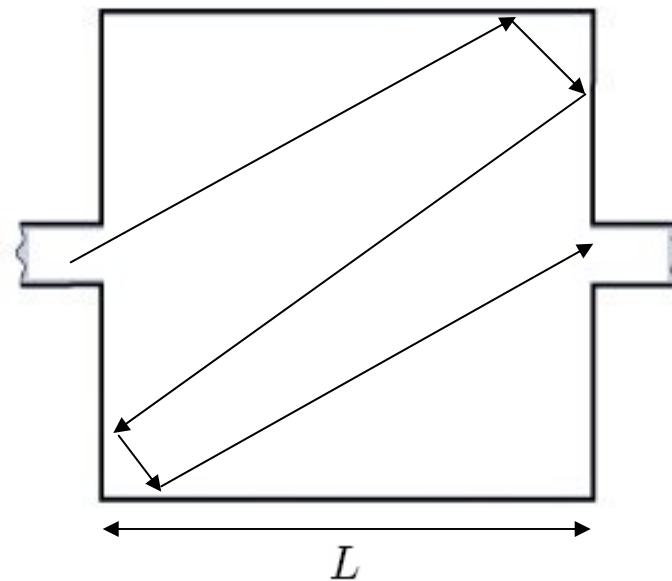
$$\ell = 7.4 \mu\text{m}$$

$$\tau_m = 38 \text{ ps}$$

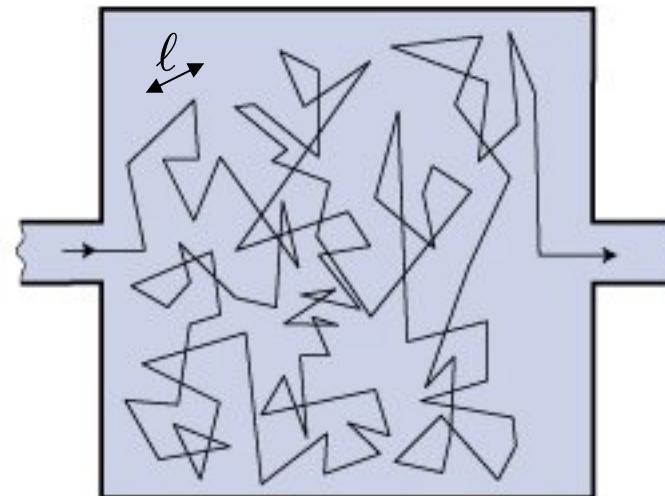
diffusion constant  $D = \frac{1}{2} v_F^2 \tau_m$

$$D = 0.72 \text{ m}^2/\text{s}$$

*ballistic*       $\ell \gg L$



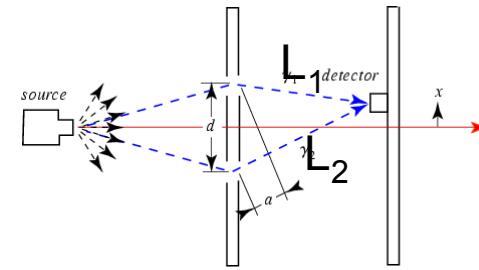
*diffusive*       $\ell \ll L$



# Mesoscopic Time and Length Scales

Phase coherence time  $\tau_\varphi$

interference  $|A_1 + A_2|^2 \sim \text{Re} \exp(i k_F(L_1 - L_2) + i(\varphi_1 - \varphi_2))$



phase coherence length  $L_\varphi$

interference suppressed to  $1/e$   
 $\exp(-L/L_\varphi)$

phase coherence time  $\tau_\varphi$

$L_\varphi = v_F \tau_\varphi$       ballistic

$L_\varphi = \sqrt{D \tau_\varphi}$       diffusive

due to interactions...  $\varphi(t)$  randomized

$$\langle \varphi \rangle_t = \int_0^t \varphi(\tau) d\tau \sim 0$$

$$\langle \exp(i\varphi(\tau)) \rangle_t \sim \exp(-t/\tau_\varphi)$$

quasi one-dimensional  $L \ll L_\varphi$

# Mesoscopic Time and Length Scales

## Phase coherence time $\tau_\varphi$

finite due to coupling of electrons to environment:

dynamic scattering mechanisms

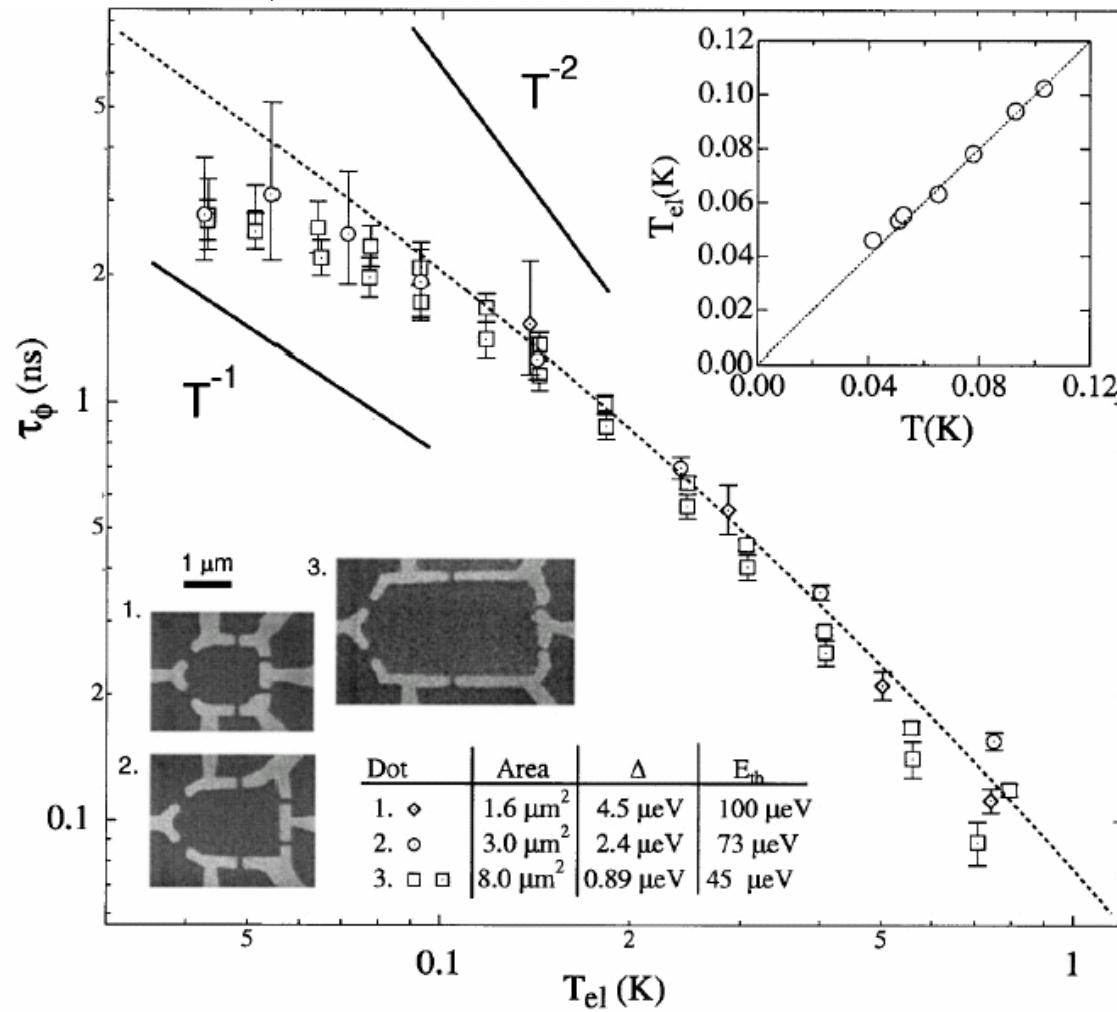
- electron phonon scattering
- electron – electron scattering
  - a) large energy exchange
  - b) quasi elastic scattering (Nyquist mechanism)
- spin flip scattering (magnetic impurities)
- electron – photon scattering
- etc

$$\tau_\varphi = \tau_\varphi(T)$$

# Mesoscopic Time and Length Scales

## Phase coherence time $\tau_\varphi$

Huibers et al., PRL 1999



$$\tau_\varphi [\text{ns}] = (4.0T[K] + 9.0T[K]^2)^{-1}$$

e-e direct

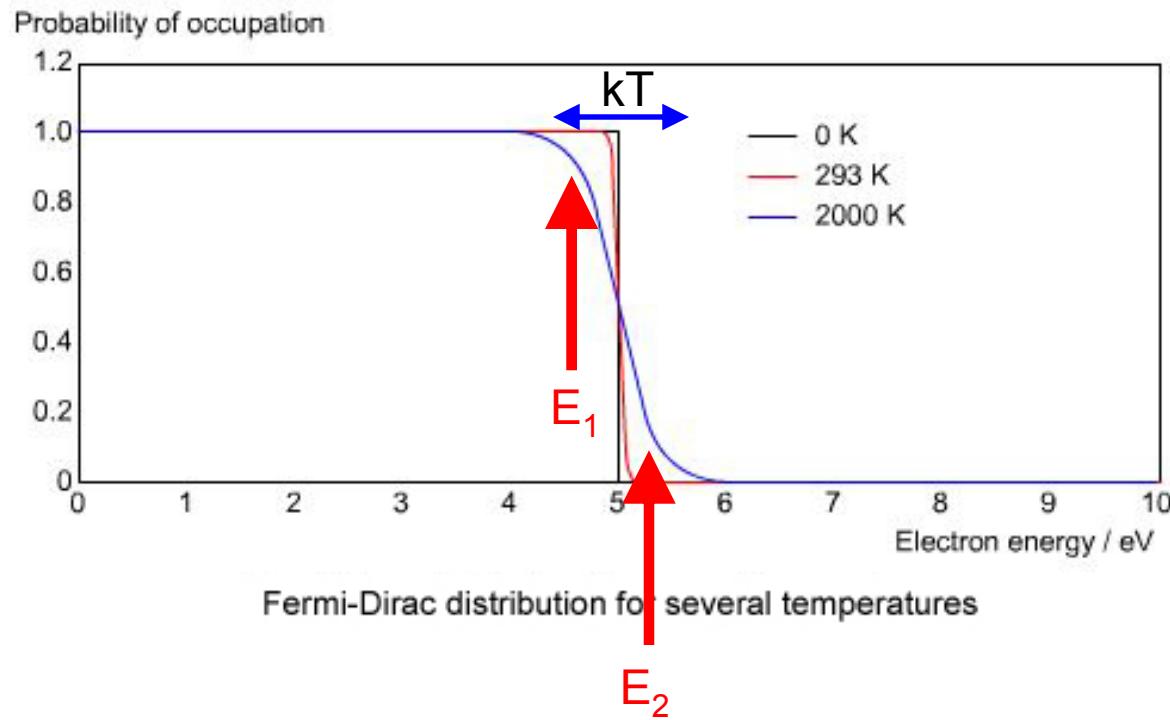
$$\tau_{ee}^{-1} = \frac{\pi}{4} \frac{(k_B T)^2}{\hbar E_F} \ln \frac{E_F}{k_B T}$$

e-e quasi-elastic (Nyquist)

$$\tau_{\phi N}^{-1} = \frac{k_B T}{2\pi\hbar} \frac{\lambda_F}{\ell_e} \ln \frac{\pi\ell_e}{\lambda_F}$$

e-phonon: small ( $T < 1\text{K}$ )

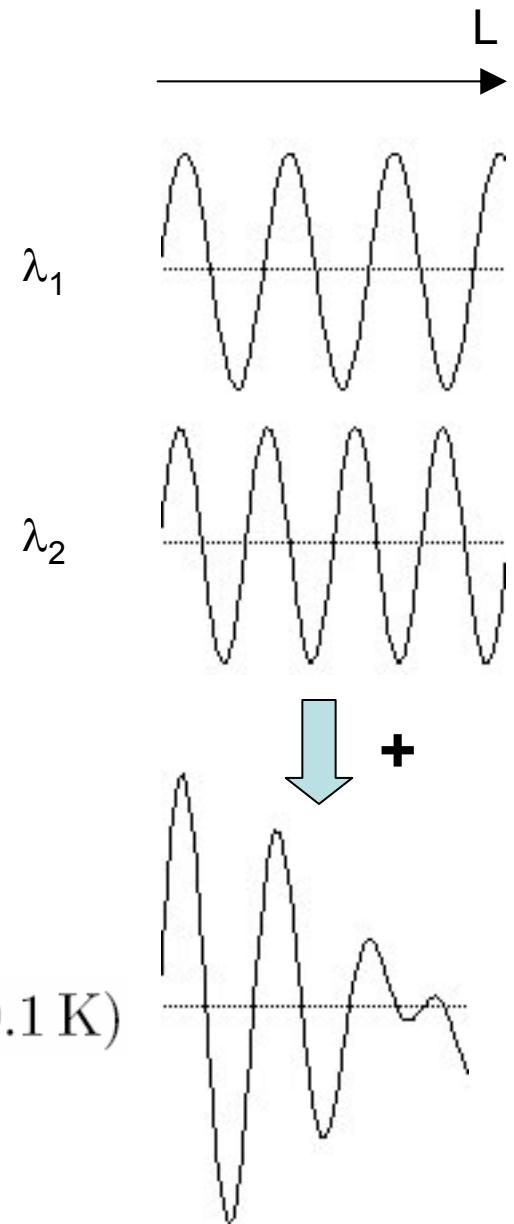
## Thermal length $L_T$ : thermal smearing



$$(k(E_F + kT) - k(E_F))x = 1$$

ballistic  $L_T = \frac{\hbar v_F}{kT}$   $L_T \sim 7.4 \mu\text{m}$  (for  $T = 0.1 \text{ K}$ )

diffusive  $L_T = \sqrt{\frac{\hbar D}{kT}}$



## Interaction parameter $r_S$

ratio of Coulomb energy to kinetic energy

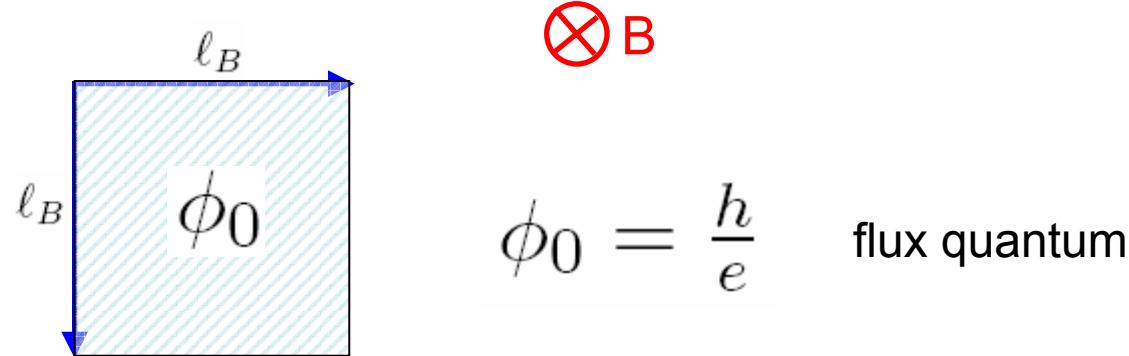
$$r_S = \frac{e^2}{4\pi\epsilon_0\epsilon r} \div E_F = \frac{e^2 m^*}{\epsilon\epsilon_0 h^2} \frac{1}{\sqrt{n}} \sim 0.7$$

characterizes “strength” of electron interactions

non interacting                       $r_s \rightarrow 0$   
weakly interacting

strongly interacting               $r_s \gtrsim 1$

## Magnetic Length $\ell_B$

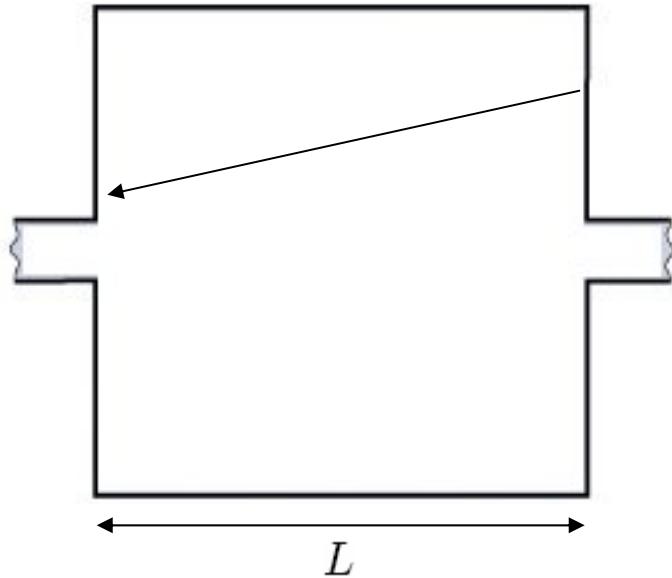


$$\text{magnetic flux} = A \cdot B = L^2 \cdot B$$

$$\ell_B = \sqrt{\frac{\hbar}{eB}}$$

# Thouless Energy

*ballistic*       $\ell \gg L$



crossing time:  $L/v_F$

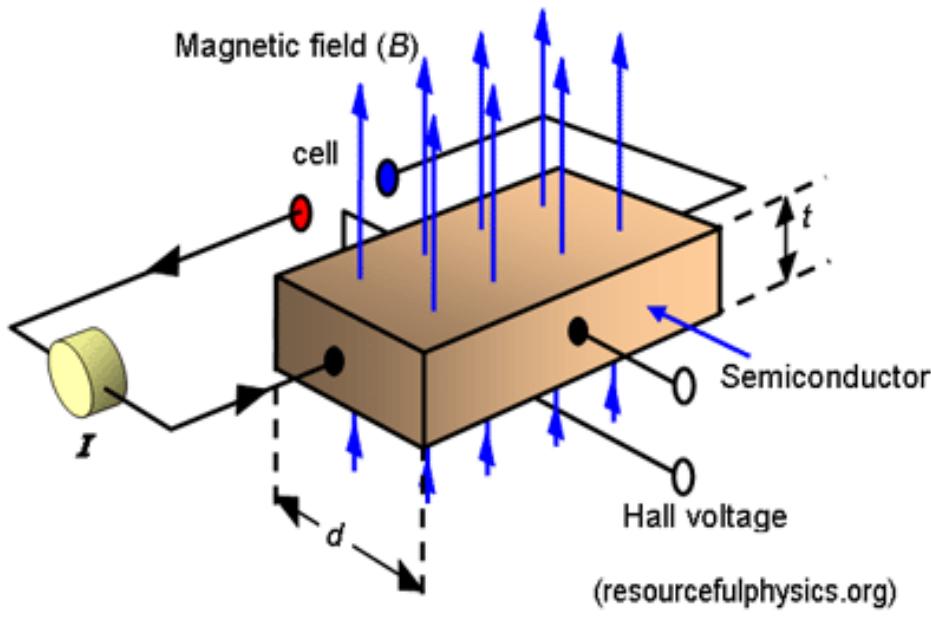
Thouless energy:  $E_T = \frac{\hbar V_F}{L}$

$$E_T = \frac{\hbar V_F}{\sqrt{A}}$$

TABLE I Electronic properties of the 2DEG in GaAs-AlGaAs heterostructures and Si inversion layers.

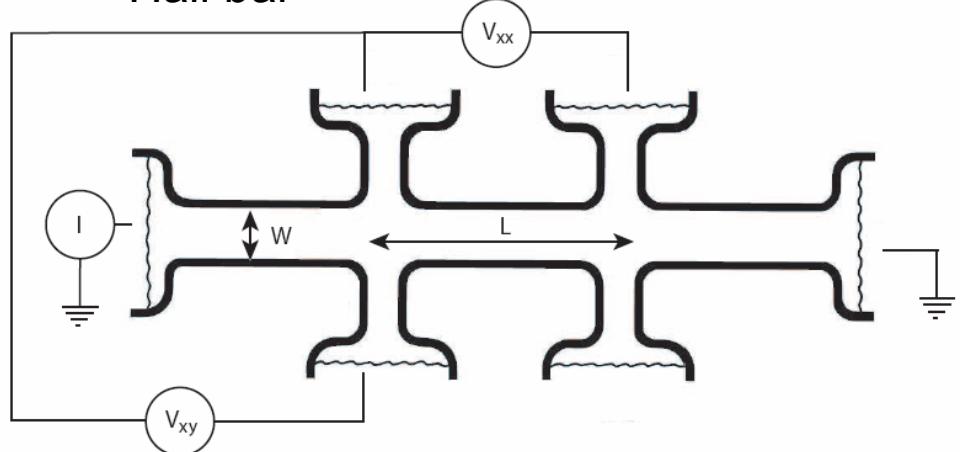
		GaAs(100)	Si(100)	Units
Effective Mass	$m$	0.067	0.19	$m_e = 9.1 \times 10^{-28}$ g
Spin Degeneracy	$g_s$	2	2	
Valley Degeneracy	$g_v$	1	2	
Dielectric Constant	$\epsilon$	13.1	11.9	$\epsilon_0 = 8.9 \times 10^{-12}$ Fm $^{-1}$
Density of States	$\rho(E) = g_s g_v (m/2\pi\hbar^2)$	0.28	1.59	$10^{11}$ cm $^{-2}$ meV $^{-1}$
Electronic Sheet Density <sup>a</sup>	$n_s$	4	1–10	$10^{11}$ cm $^{-2}$
Fermi Wave Vector	$k_F = (4\pi n_s/g_s g_v)^{1/2}$	1.58	0.56–1.77	$10^6$ cm $^{-1}$
Fermi Velocity	$v_F = \hbar k_F/m$	2.7	0.34–1.1	$10^7$ cm/s
Fermi Energy	$E_F = (\hbar k_F)^2/2m$	14	0.63–6.3	meV
Electron Mobility <sup>a</sup>	$\mu_e$	$10^4 - 10^6$	$10^4$	cm $^2$ /Vs
Scattering Time	$\tau = m\mu_e/e$	0.38–38	1.1	ps
Diffusion Constant	$D = v_F^2 \tau / 2$	140–14000	6.4–64	cm $^2$ /s
Resistivity	$\rho = (n_s e \mu_e)^{-1}$	1.6–0.016	6.3–0.63	kΩ
Fermi Wavelength	$\lambda_F = 2\pi/k_F$	40	112–35	nm
Mean Free Path	$l = v_F \tau$	$10^2 - 10^4$	37–118	nm
Phase Coherence Length <sup>b</sup>	$l_\phi = (D\tau_\phi)^{1/2}$	200–...	40–400	nm(T/K) $^{-1/2}$
Thermal Length	$l_T = (\hbar D/k_B T)^{1/2}$	330–3300	70–220	nm(T/K) $^{-1/2}$
Cyclotron Radius	$l_{cycl} = \hbar k_F/eB$	100	37–116	nm(B/T) $^{-1}$
Magnetic Length	$l_m = (\hbar/eB)^{1/2}$	26	26	nm(B/T) $^{-1/2}$
	$k_F l$	15.8–1580	2.1–21	
	$\omega_c \tau$	1–100	1	(B/T)
	$E_F/\hbar\omega_c$	7.9	1–10	(B/T) $^{-1}$

# Classical Hall Effect



2D: thickness  $t$  drops out

Hall bar

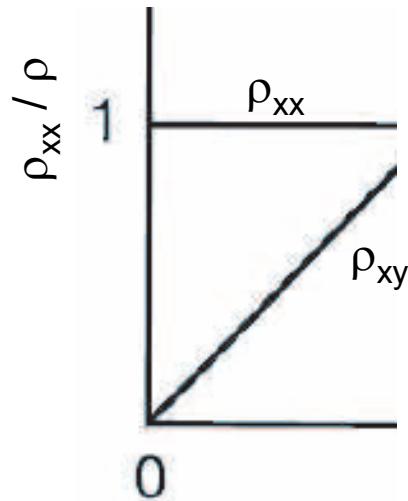
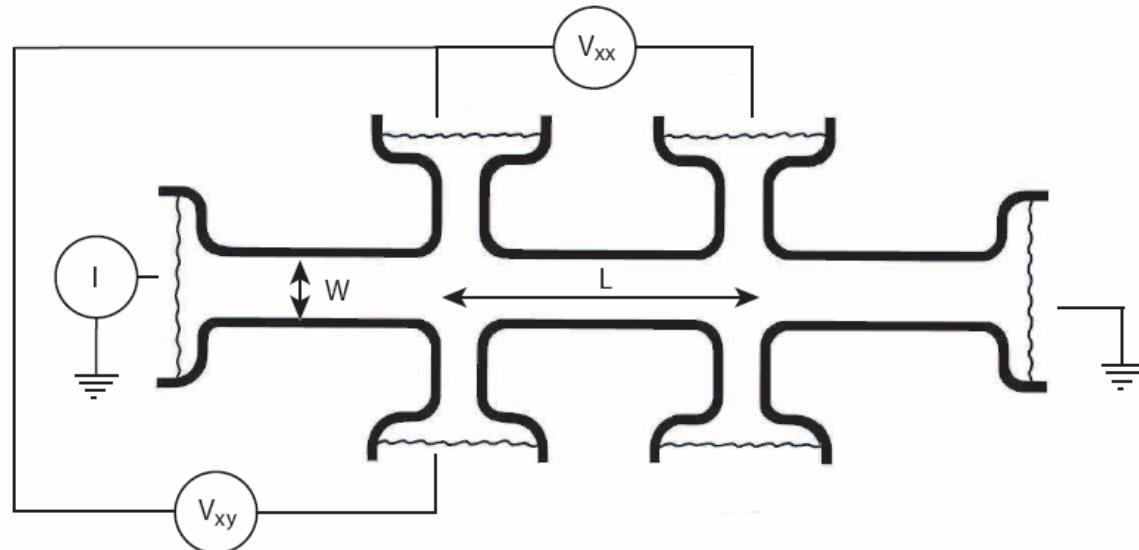


$$\frac{m^* v_d}{\tau_m} = e [E + v_d \wedge B]$$

$$\begin{pmatrix} \frac{m^*}{e\tau_m} & -B \\ +B & \frac{m^*}{e\tau_m} \end{pmatrix} \begin{pmatrix} v_x \\ v_y \end{pmatrix} = \begin{pmatrix} E_x \\ E_y \end{pmatrix}$$

$$\rho_{xx} = \sigma^{-1}, \quad \rho_{xy} = -\rho_{yx} = -\frac{B}{en}$$

# Classical Hall Effect



$$V_x = R_{xx} I_x \quad R_{xx} = \frac{L}{W} \rho_{xx}$$

$$V_H = V_y = \rho_{yx} I_x = \frac{B}{en} I_x = R_H I_x \quad R_H = B/(en)$$

$$R_H \sim 3.1 \text{ k}\Omega/\text{Tesla} \text{ for } n \sim 2 \times 10^{-11} \text{ cm}^{-2}$$

$$\mu = (neR_{xx}W/L)^{-1}$$

# Quantum Hall Effect

## Phenomenological Treatment

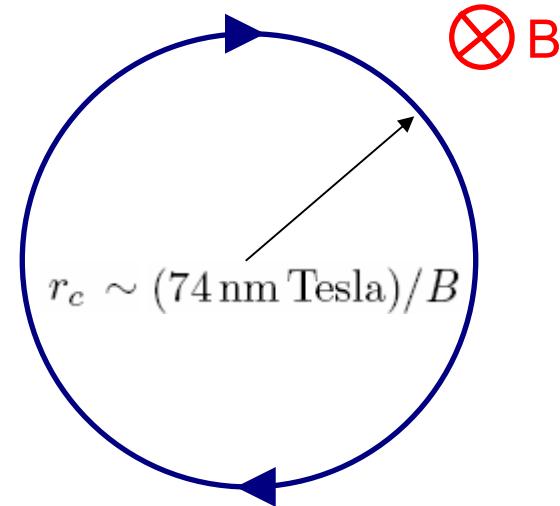
Lorentz-Force  $F = ev \times B$

zentrifugal force  $m\omega^2 r$

$$evB = m\omega^2 r$$

$$\omega_c = \frac{eB}{m^*}, \quad r_c = \frac{v}{\omega_c}$$

cyclotron frequency, radius



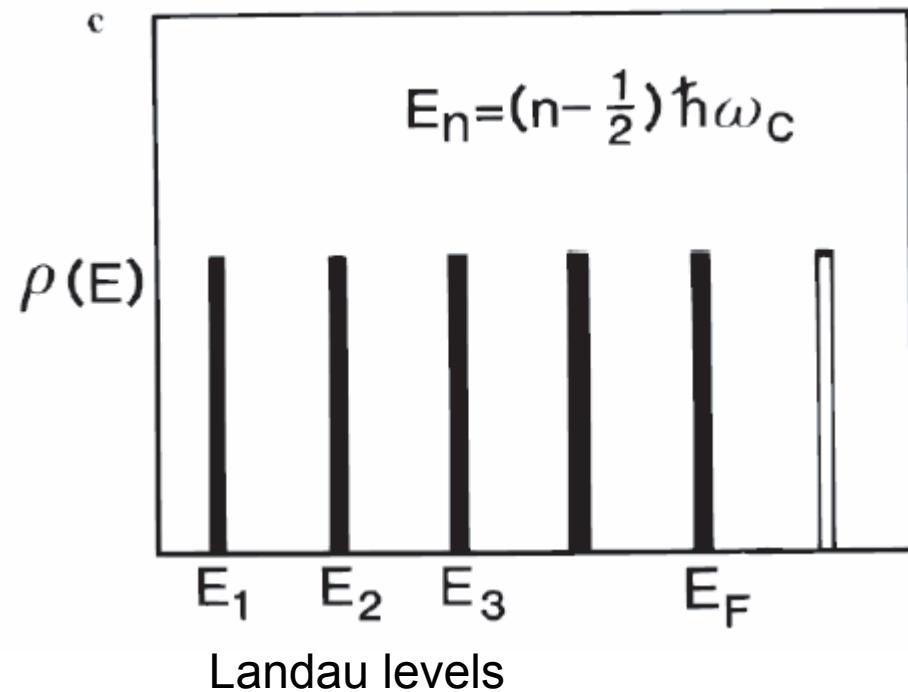
$$r_c \sim (74 \text{ nm Tesla})/B$$

$$\begin{aligned} \hbar\omega_c &= (1.73 \text{ meV/Tesla}) \\ 1 \text{ meV}/k_B &= 11.6K \end{aligned}$$

$$\text{quantization condition: circumference} = N \lambda_F \quad \rightarrow \quad E_n = n \frac{1}{2} \hbar\omega_c$$

# Quantum Hall Effect

density of states



$$\rho_{DOS}(E, B) = N_0 \sum_{n=0}^{\infty} \delta(E - (n + 1/2)\hbar\omega_c)$$

$N_0$  number of states per area in each Landau level

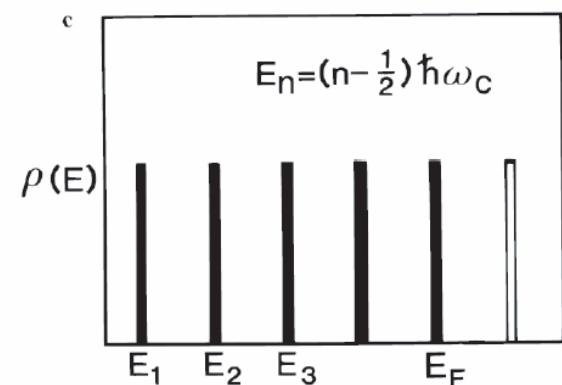
# Quantum Hall Effect

all zero field states within range in energy of  $\hbar\omega_c$  condense in one Landau level

$$N_0 = \hbar\omega_c \times (m/(\pi\hbar^2)) = 2eB/h.$$

Landau level filling factor

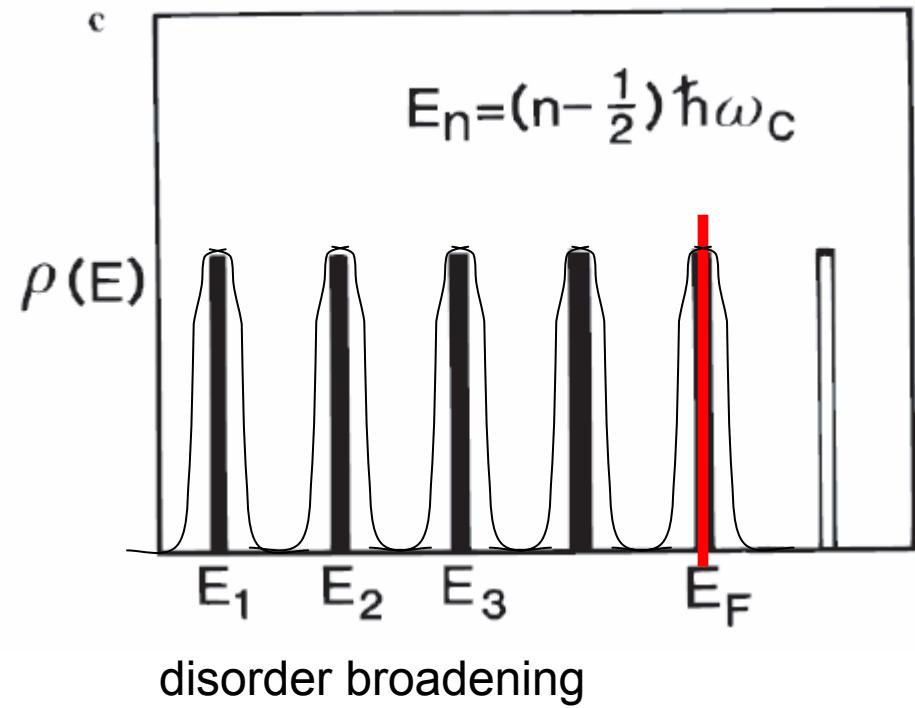
$$\nu = \frac{n}{2eB/h}$$



number  $N$  of Landau levels with  $E < E_F$  : integer

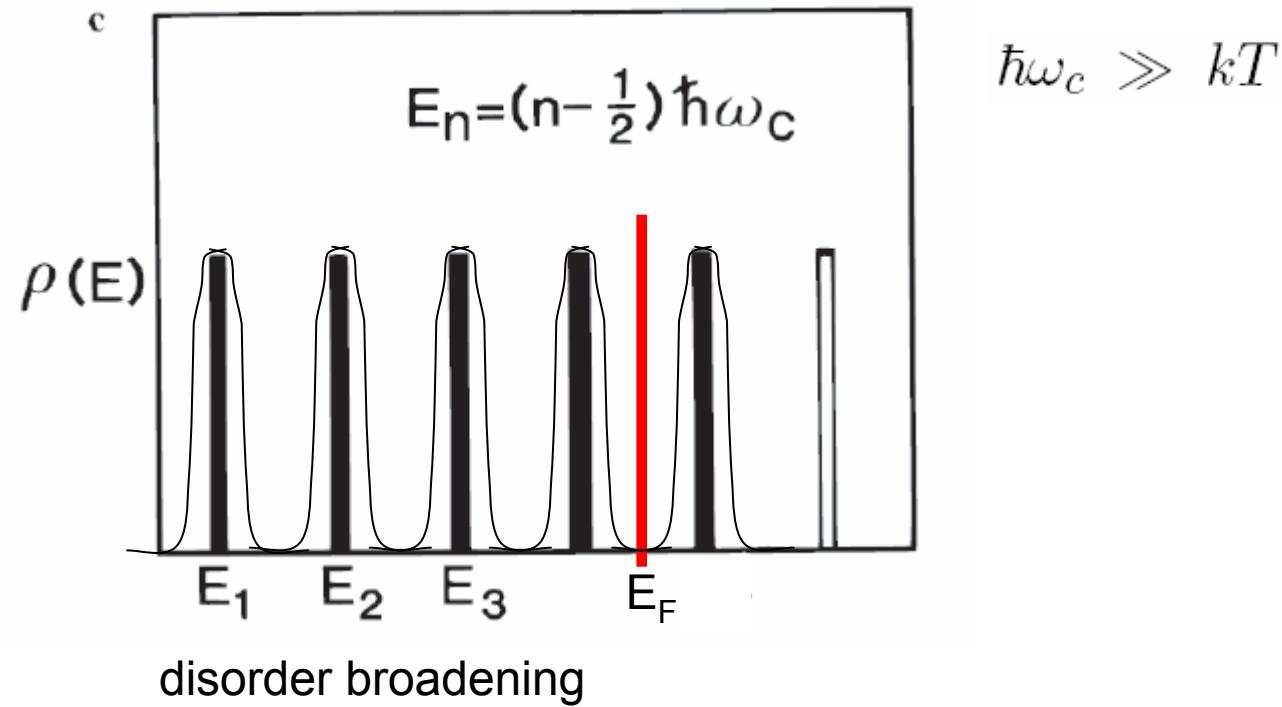
# Quantum Hall Effect: Transport

$v = N$  : scattering possible, resistance

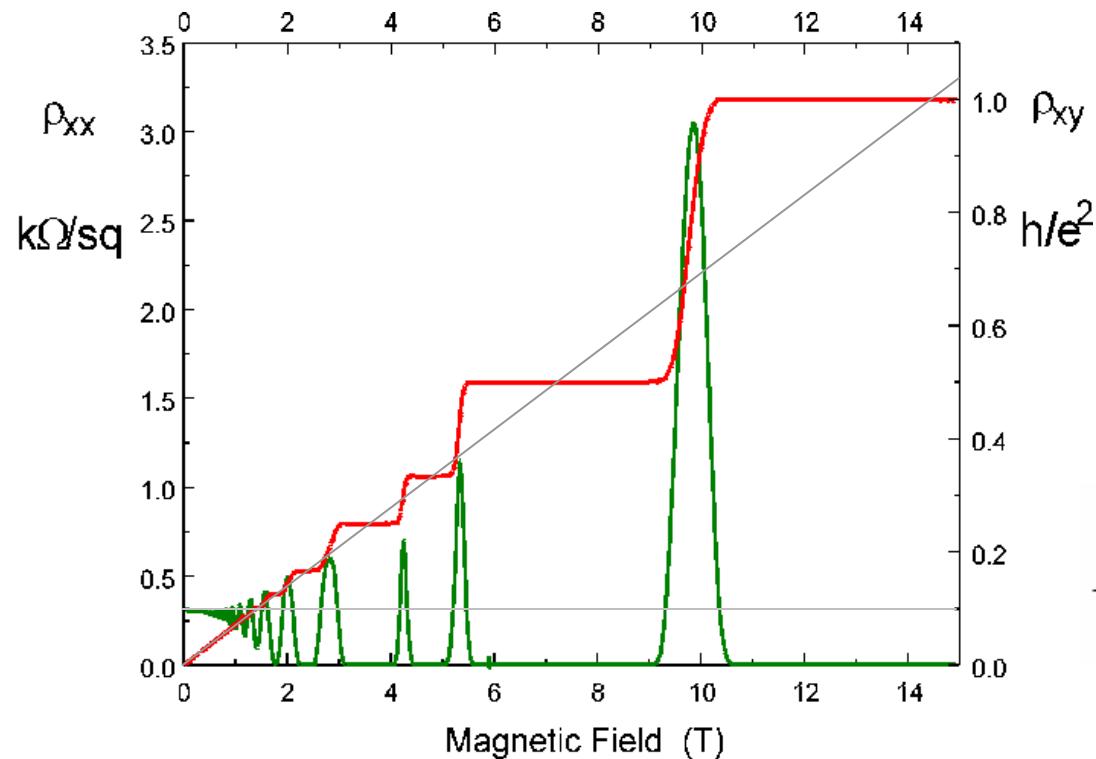
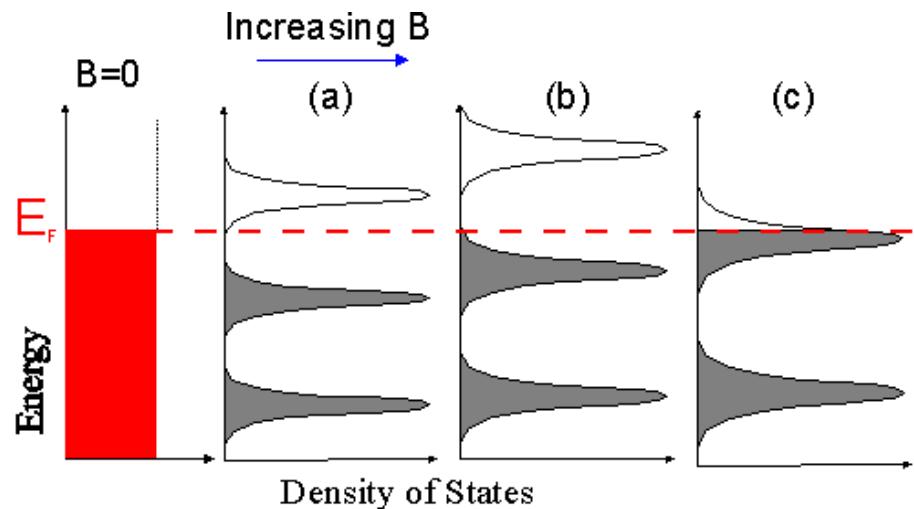


# Quantum Hall Effect: Transport

$v \ll N$  : scattering NOT possible, ZERO resistance ( $\rho_{xx}$ )



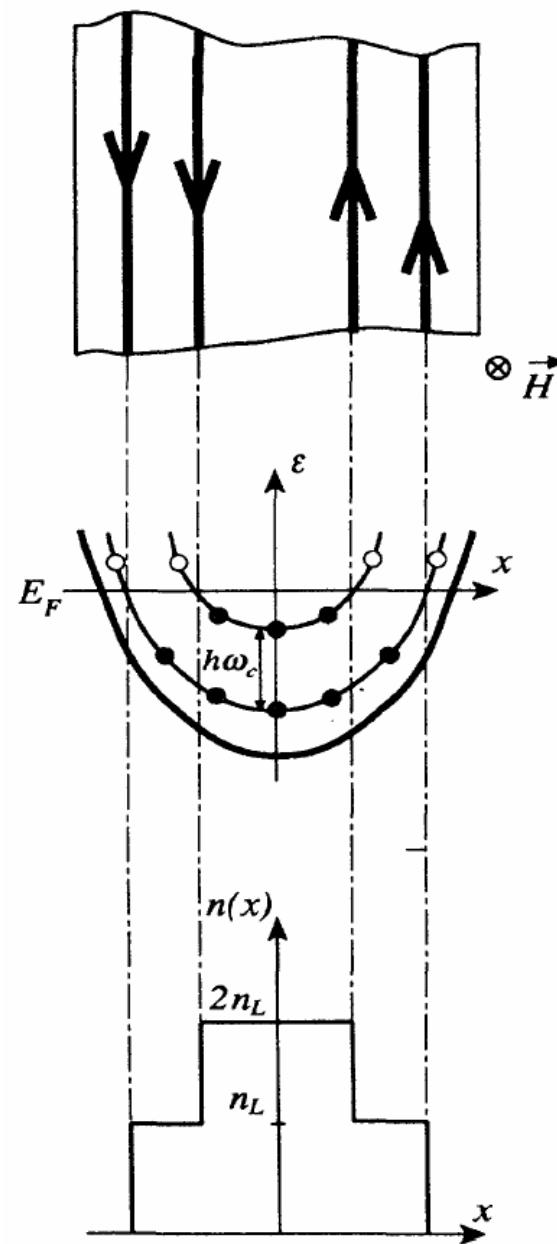
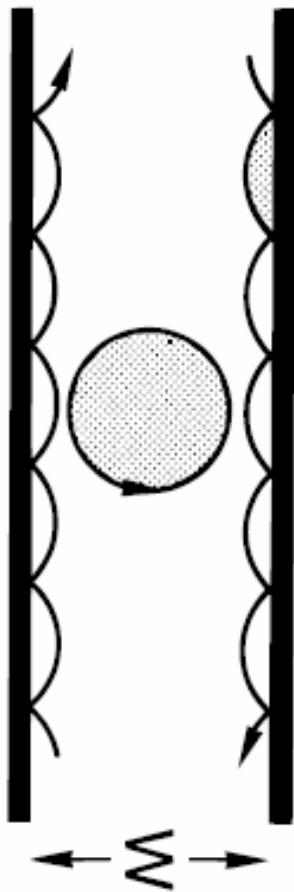
# Quantum Hall Effect: B dependence



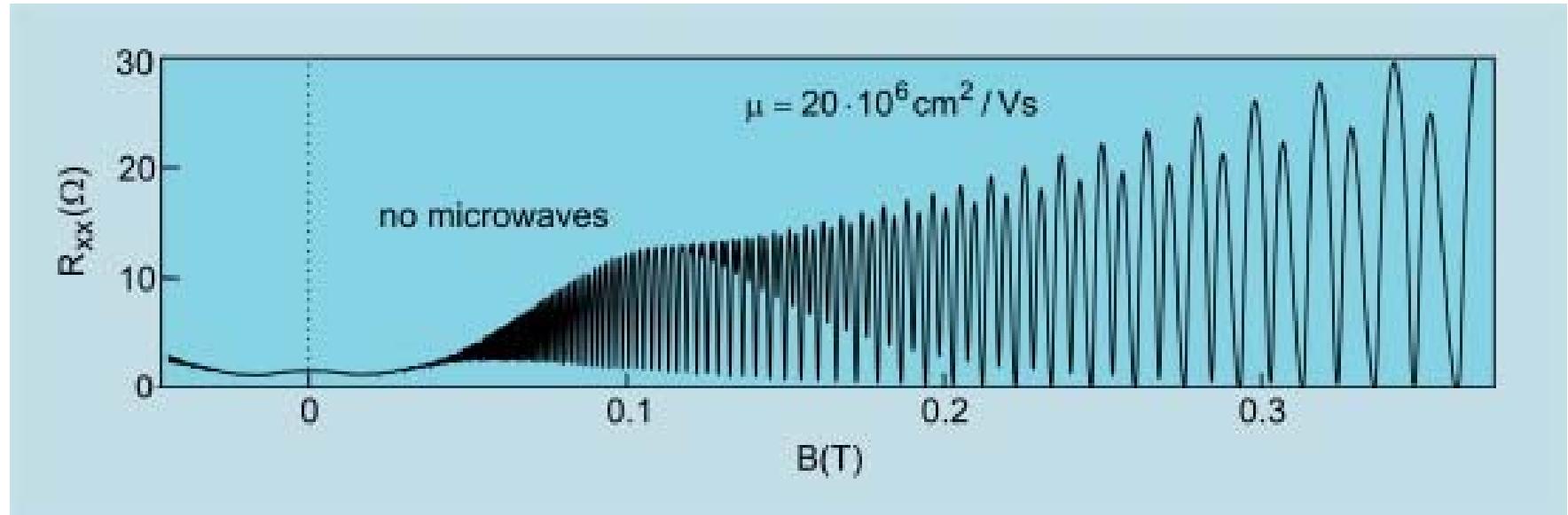
Integer Quantum Hall Effect

$$R_H = \frac{1}{g_s g_v} \frac{h}{e^2} \frac{1}{N} = \frac{h}{2e^2} \frac{1}{N}$$

# Quantum Hall Effect: edge states / skipping orbits



# Shubnikov-de-Haas Oscillations



$\hbar\omega_c > kT, \hbar/\tau_m$  orbital Landau levels

$g\mu_B B > kT, \hbar/\tau_m$  spin polarized Landau levels

# Quantum Mechanical Treatment

$$\left[ \frac{(i\hbar\nabla + eA)^2}{2m^*} + U(y) \right] \psi(x, y) = E\psi(x, y)$$

$$A = -\hat{x}By \quad \rightarrow \quad A_x = -By \quad \text{and} \quad A_y = 0.$$

three cases:

- free electrons in magnetic field ( $U = 0$ )
- confined,  $B = 0$  (constriction, QPC)
- confined *and* in magnetic field

$$\left[\frac{(i\hbar\nabla+eA)^2}{2m^*}+U(y)\right]\psi(x,y)=E\psi(x,y)$$

$$p_x=-i\hbar\frac{\partial}{\partial x}\quad\text{and}\quad p_y=i\hbar\frac{\partial}{\partial y}$$

$$\left[\frac{(p_x+eBy)^2}{2m^*}+\frac{p_y^2}{2m^*}+U(y)\right]\psi(x,y)=E\psi(x,y)$$

$$\psi(x,y)=\frac{1}{\sqrt{L}}\exp(ikx)\chi(y)$$

$$\left[\frac{(\hbar k+eBy)^2}{2m^*}+\frac{p_y^2}{2m^*}+U(y)\right]\chi(y)=E\chi(y)$$

## Free electrons in a magnetic field

$$U \equiv 0$$

$$\left[ \frac{p_y^2}{2m^*} + \frac{1}{2}m^*\omega_c^2(y + y_k)^2 \right] \chi(y) = E\chi(y)$$

harmonic oscillator

$$y_k = \frac{\hbar k}{eB} \quad \text{and} \quad \omega_c = \frac{eB}{m^*}$$

... textbook ...

$$E(n, k) = \left( n + \frac{1}{2} \right) \hbar\omega_c, \quad n = 0, 1, 2, \dots$$

zero point energy  
pure quantum effect  
no classical analog

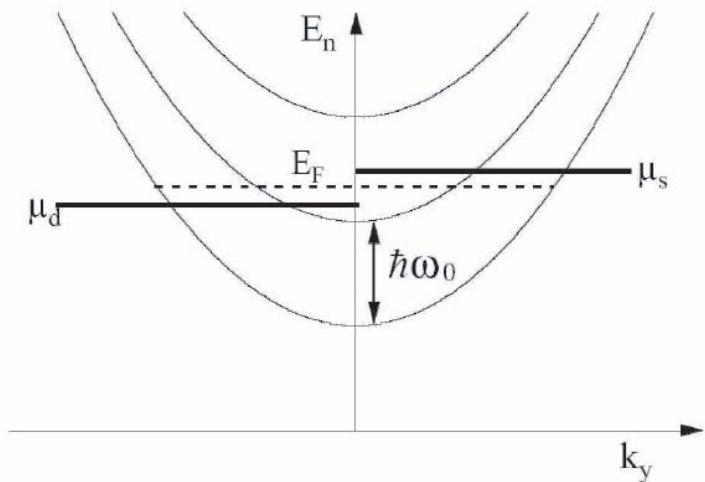
# Electrons Confined in a Constriction

$$U = 1/2m^*\omega_0^2 y^2$$

$$\left[ \frac{\hbar^2 k^2}{2m^*} + \frac{p_y^2}{2m^*} + \frac{1}{2} m^* \omega_0^2 y^2 \right] \chi(y) = \chi(y)$$

... textbook ...

$$E(n, k) = \frac{\hbar^2 k^2}{2m^*} + \left( n + \frac{1}{2} \right) \hbar\omega_c, \quad n = 0, 1, 2, \dots$$



$$V_{sd} = (\mu_s - \mu_d)/e$$

$$v(n, k) = \frac{1}{\hbar} \frac{\partial E(n, k)}{\partial k} = \frac{\hbar k}{m^*}$$

as for free electrons

## Transport through a Constriction

$$I = e \sum_{n=1}^N \int_{\mu_d}^{\mu_s} dE \frac{1}{2} \rho_n(E) v_n(E) T_n(E)$$

$\rho_n(E) = 2/\pi(dE_n/dk_x)^{-1}$  1D density of states

$T_n(E)$  transmission probability of the  $n^{\text{th}}$  subband

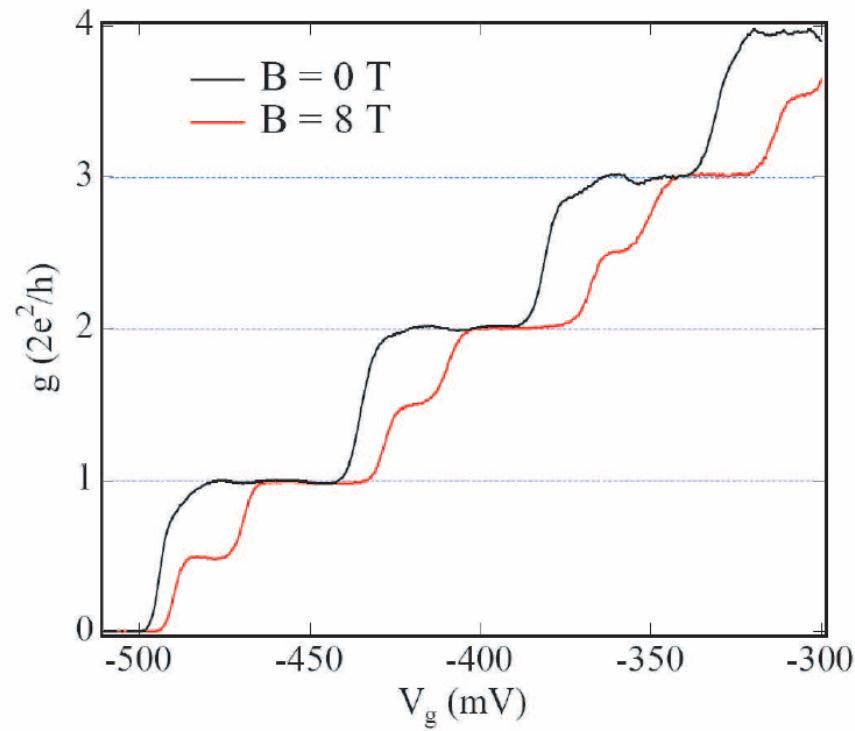
$$\begin{aligned} I &= e \sum_{n=1}^N \int_{\mu_d}^{\mu_s} dE \frac{1}{2} \frac{2}{\pi} \left( \frac{\partial E_n}{\partial k_x} \right)^{-1} \frac{1}{\hbar} \frac{\partial E_n}{\partial k_x} T_n(E_F) \\ &= \frac{2e}{h} \sum_{n=1}^N T_n(E_F) \int_{\mu_d}^{\mu_s} dE \\ &= \frac{2e}{h} \sum_{n=1}^N T_n(E_F) eV_{sd}. \end{aligned}$$

**QUANTIZED!!**

# Transport through a Constriction: Conductance Quantization

$$G = \frac{2e^2}{h} \sum_{n=1}^N T_n(E_F) \quad \sum_{n=1}^N T_n(E_F) = 1$$

$$G = \frac{2e^2}{h} N$$



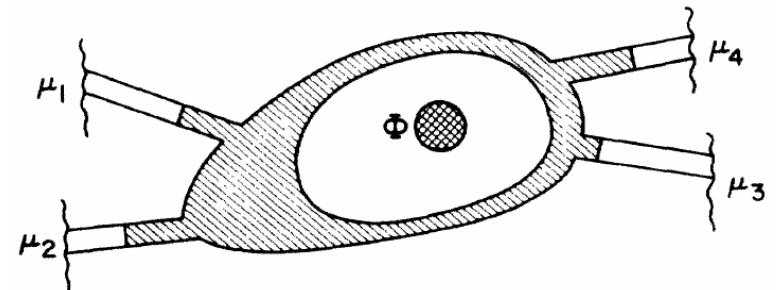
# Landau-Büttiker Formalism

matrix  $\mathbf{t}$

$$T_n(E_F) = \sum_{m=1}^N |t_{mn}|^2 \quad \text{two-terminal}$$

$$T_{\alpha \rightarrow \beta} = \sum_{n=1}^{N_\alpha} \sum_{m=1}^{N_\beta} |t_{\beta\alpha,mn}|^2 \quad \text{multi terminal}$$

$t_{\beta\alpha,mn}$  transmission probability amplitude from mode  $n$  in lead  $\alpha$  to mode  $m$  in lead  $\beta$



greek: leads  
roman: modes

$$G = \frac{2e^2}{h} \sum_{n=1}^N T_n(E_F) = \frac{2e^2}{h} \sum_{n,m=1}^N |t_{mn}|^2 = \frac{2e^2}{h} \operatorname{Tr} \mathbf{t} \mathbf{t}^\dagger$$